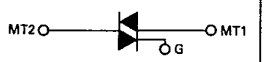
SC260
SC260( )3
SC261

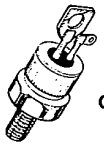
Triacs
Bidirectional Triode Thyristors

. . . designed primarily for industrial and military applications for the control of ac loads in applications such as light dimmers, power supplies, heating controls, motor controls, welding equipment and power switching systems; or wherever full-wave, silicon gate controlled solid-state devices are needed.

- All Diffused and Glass Passivated Junctions for Greater Stability
- Pressfit, Stud and Isolated Stud Packages
- Gate Triggering Guaranteed In All 3 Quadrants

TRIACs
25 AMPERES RMS
200 thru 600 VOLTS





CASE 263-04
STYLE 2
SC260

CASE 310-02
STYLE 2
SC261

CASE 311-02
STYLE 2
SC260( )3

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Repetitive Peak Off-State Voltage (T_C = −40°C to +115°C) SC260B, SC260B3, SC261B SC260D, SC260D3, SC261D SC260M, SC260M3, SC261M	V_{DRM}	 200 400 600	Volts
RMS On-State Current	$I_{T(RMS)}$	25	Amps
Peak Non-Repetitive Surge Current (One Cycle, 60 Hz)	I_{TSM}	250	Amps
Circuit Fusing Considerations t = 1 ms t = 8.3 ms	I^2t	 150 260	A^2s
Peak Gate Power (Pulse Width = 10 μs)	P_{GM}	10	Watts
Average Gate Power	$P_{G(AV)}$	0.5	Watt
Peak Gate Power	I_{GM}	2	Amps
Operating Junction Temperature Range	T_J	−40 to +115	°C
Storage Temperature Range	T_{stg}	−40 to +125	°C
Stud Torque	—	30	in. lb.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case SC260, SC261 SC260( )3	$R_{\theta JC}$	 1.8 1.95	°C/W

ELECTRICAL CHARACTERISTICS (T_C = +25°C unless otherwise noted. Values apply for either polarity of Main Terminal 2 Characteristics referenced to Main Terminal 1.)

Characteristic	Symbol	Min	Typ	Max	Unit
Peak Forward or Reverse Blocking Current (Rated V_{DRM} or V_{RRM}, gate open) T_C = 25°C	I_{DRM}, I_{RRM}	—	—	10	μA
T_C = +115°C		—	—	1	mA
Peak On-State Voltage (I_{TM} = 35 A Peak, Pulse Width = 1 ms, Duty Cycle ≤ 2%)	V_{TM}	—	—	1.58	Volts
Critical Rate of Rise of Off-State Voltage (Rated V_{DRM}, Gate Open-Circuited, Exponential Waveform) T_C = +115°C	dv/dt	50	—	—	V/μs
Critical Rate-of-Rise of Commutating Off-State Voltage ($I_{T(RMS)}$ = Rated RMS On-State Current) (V_{DRM} = Rated Peak Off-State Voltage, Gate Open-Circuited, Commutating di/dt = 13.5 A/ms) T_C = +80°C	dv/dt(c)	5	—	—	V/μs
DC Gate Trigger Current (Continuous dc) (V_D = 12 Vdc)	I_{GT}				mAdc
MT2(+), G(+); MT2(−), G(−); R_L = 100 Ohms		—	—	50	
MT2(+), G(−); R_L = 50 Ohms		—	—	50	
DC Gate Trigger Current (Continuous dc) (V_D = 12 Vdc) T_C = −40°C	I_{GT}				mAdc
MT2(+), G(+); MT2(−), G(−); R_L = 50 Ohms		—	—	80	
MT2(+), G(−); R_L = 25 Ohms		—	—	80	
DC Gate Trigger Voltage (Continuous dc) (V_D = 12 Vdc)	V_{GT}				Vdc
MT2(+), G(+); MT2(−), G(−); R_L = 100 Ohms		—	—	2.5	
MT2(+), G(−); R_L = 50 Ohms		—	—	2.5	
DC Gate Trigger Voltage (Continuous dc) (V_D = 12 Vdc) T_C = −40°C	V_{GT}				Vdc
MT2(+), G(+); MT2(−), G(−); R_L = 50 Ohms		—	—	3.5	
MT2(+), G(−); R_L = 25 Ohms		—	—	3.5	
DC Gate Non-Trigger Voltage (V_D = Rated V_{DRM}, R_L = 1K Ohms, All Trigger Modes) T_C = 115°C	V_{GD}	0.25	—	—	Vdc
Holding Current (V_D = 24 Vdc, Peak Initiating Current = 0.5 A, Pulse Width = 0.1 to 10 ms, Gate Trigger Source = 7 V, 20 Ohms)	I_H				mAdc
T_C = +25°C		—	—	75	
T_C = −40°C		—	—	100	
Latching Current (V_D = 24 Vdc, Gate Trigger Source = 15 V, 100 Ohms, Pulse Width = 50 μs, 5 μs Maximum Rise and Fall Times)	I_L				mAdc
MT2(+), G(+); MT2(−), G(−) T_C = 25°C		—	—	100	
MT2(+), G(−) T_C = 25°C		—	—	200	
MT2(+), G(+); MT2(−), G(−) T_C = −40°C		—	—	200	
MT2(+), G(−) T_C = −40°C		—	—	400	

FIGURE 1 – CURRENT DERATING

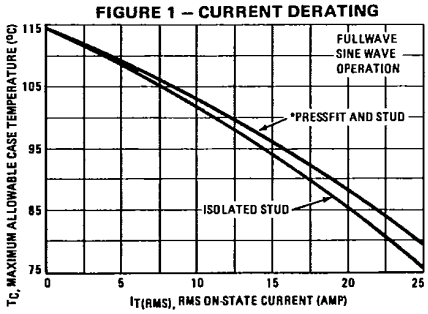


FIGURE 2 – MAXIMUM ON-STATE POWER DISSIPATION